

ABSTRACT OF THE DISCLOSURE

First wirings and first dummy wirings are formed in a p-SiOC film formed on a substrate. A p-SiOC film is formed, and a cap film
5 is formed on the p-SiOC film. A dual damascene wiring, including vias connected to the first wirings and the second wirings, is formed in the cap film and the p-SiOC film 22. Dummy vias are formed on the periphery of isolated vias.